

Claims

- [c1] 1. A field effect transistor (FET) comprising:
 - a source region;
 - a drain region;
 - a channel region disposed between the source and drain regions;
 - a bifurcated gate region positioned over said channel region; and
 - a gate oxide layer adjacent to said gate region, wherein said gate oxide layer comprises an alkali metal ion.
- [c2] 2. The transistor of claim 1, further comprising:
 - a substrate;
 - an isolation layer positioned over said substrate; and
 - at least one fin structure disposed between the source and drain regions;
 - wherein said source and drain regions are positioned over said isolation layer.
- [c3] 3. The transistor of claim 1, wherein said alkali metal ion comprises any of cesium and rubidium.
- [c4] 4. The transistor of claim 1, wherein said transistor comprises a CMOS (complementary metal oxide semiconductor).

tor) device.

- [c5] 5.The transistor of claim 4, wherein said CMOS device comprises any of a nFET configuration and a pFET configuration.
- [c6] 6.The transistor of claim 5, further comprising ion implantation levels for each of said nFET configuration and said pFET configuration of approximately $3 \times 10^{18} \text{ cm}^{-3}$.
- [c7] 7.The transistor of claim 1, wherein said gate region comprises silicide.
- [c8] 8.The transistor of claim 5, wherein said alkali metal ion adjusts nFET and pFET threshold voltages for the nFET and pFET configurations by an amount required to match desired off-currents for said nFET and pFET configurations.
- [c9] 9.A (field effect transistor) CMOS (complementary metal oxide semiconductor) device comprising:
 - raised source/drain regions;
 - a channel region disposed between said source/drain regions;
 - a gate region positioned over said channel region;
 - a silicon layer dividing said gate region; and
 - a gate oxide layer adjacent to said gate region, wherein

said gate oxide layer comprises an alkali metal ion.

- [c10] 10. The device of claim 9, further comprising:
 - a substrate;
 - an isolation layer positioned over said substrate; and
 - at least one fin structure disposed between the source and drain regions;
 - wherein said source/drain regions are positioned over said isolation layer.
- [c11] 11. The device of claim 9, wherein said alkali metal ion comprises any of cesium and rubidium.
- [c12] 12. The device of claim 9, further comprising any of a nFET region and a pFET region.
- [c13] 13. The device of claim 12, comprising ion implantation levels for each of said nFET region and pFET region of approximately $3 \times 10^{18} \text{ cm}^{-3}$.
- [c14] 14. The device of claim 9, further comprising spacers separating said gate region from said source/drain regions.
- [c15] 15. The device of claim 9, wherein said gate region comprises silicide.
- [c16] 16. The device of claim 12, wherein said alkali metal ion adjusts nFET and pFET threshold voltages for the nFET

and pFET regions by an amount required to match desired off-currents for said nFET and pFET regions.

- [c17] 17. A method of tuning a threshold voltage of nFET (field effect transistor) and pFET devices in a double-gate CMOS (complementary metal oxide semiconductor) integrated circuit structure, said method comprising:
 - performing a PSP (post silicide probe) electrical test on said double-gate CMOS integrated circuit structure;
 - determining nFET and pFET threshold voltages during said PSP electrical test; and
 - implanting said double-gate CMOS integrated circuit structure with an alkali metal ion.
- [c18] 18. The method of claim 17, wherein said implanting adjusts said nFET and pFET threshold voltages by an amount required to match desired off-currents for said nFET and pFET devices.
- [c19] 19. The method of claim 17, wherein prior to said performing, said method comprises:
 - forming a fin structure on a substrate;
 - forming source/drain regions over said fin structure;
 - forming a channel region between said source/drain regions;
 - depositing a gate oxide layer adjacent to said source/drain regions; and

forming a gate region over said gate oxide layer and said fin structure.

[c20] 20. The method of claim 19, further comprising forming an isolation layer on said substrate.

[c21] 21. The method of claim 17, wherein said alkali metal ion comprises any of cesium and rubidium.

[c22] 22. The method of claim 17, wherein ion implantation levels for said nFET and pFET devices are determined during said PSP test.

[c23] 23. The method of claim 17, wherein ion implantation levels for each of said nFET and pFET devices is approximately $3 \times 10^{18} \text{ cm}^{-3}$.